

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:

Varun Singh, et al.

Serial No.: Not Assigned

Filed: Herewith

For: AN IMPROVED POLYSILICON RESISTOR HAVING ADJUSTABLE TEMPERATURE COEFFICIENTS AND THE METHOD OF MAKING THE SAME

BOX: Patent Application
Assistant Commissioner For Patents
Washington, D.C. 20231

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Dear Sir:

PRELIMINARY AMENDMENT

Prior to the examination of the above-identified application, please amend this application as follows:

IN THE CLAIMS

Please cancel Claims 3-10 and 13-15. Claims 1-2 and 11-12 remain for consideration in this application.

1. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from $\sim 6 \times 10^{19} \text{ cm}^{-3}$ to $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$.

2. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than $\sim 3.75 \times 10^{20} \text{ cm}^{-3}$.

11. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of greater than $\sim 6 \times 10^{19} \text{ cm}^{-3}$.

12. A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique.

REMARKS

In view of the above, it is believed that this application is in condition for allowance, and such a Notice is respectfully requested.

Respectfully submitted,

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